## **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP0160A uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

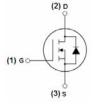
#### **General Features**

- $V_{DS}$  =100V, $I_{D}$  =60A  $R_{DS(ON)}$ =8.5m $\Omega$  (typical) @  $V_{GS}$ =10V  $R_{DS(ON)}$ =10.4m $\Omega$  (typical) @  $V_{GS}$ =4.5V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

#### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



#### Schematic diagram



#### Marking and pin assignment



TO-220-3L top view

**Package Marking and Ordering Information** 

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0160A	NCEP0160A	TO-220	-	-	-

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	60	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	42.4	Α
Pulsed Drain Current	I <sub>DM</sub>	240	А
Maximum Power Dissipation	P <sub>D</sub>	105	W
Derating factor		0.7	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	210	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 175	$^{\circ}$ C

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.42	°C/W
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# NCEP0160A

## Electrical Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

Parameter	ter Symbol Condition		Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	V <sub>GS</sub> =0V I <sub>D</sub> =250μA 100		-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.7	2.2	V	
Drain-Source On-State Resistance	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	8.5	10.0	mΩ	
Dialii-Source Oil-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5V, $I_D$ =20A	-	10.4	12.0	mΩ	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	-	30	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C <sub>lss</sub>	\/ -50\/\/ -0\/	-	3050	-	PF	
Output Capacitance	Coss	$V_{DS}$ =50V, $V_{GS}$ =0V, F=1.0MHz	-	274	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVITZ	-	17.8	-	PF	
Switching Characteristics (Note 4)	Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	11	-	nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =50V, $I_D$ =20A	-	7	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10 $V$ , $R_{G}$ =1.6 $\Omega$	-	30	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS	
Total Gate Charge	Qg	\/ _F0\/	-	45	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =50V,I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	11.6	-	nC	
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	6	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	60	Α	
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = I_S$	-	78	-	nS	
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	149	-	nC	

#### Notes:

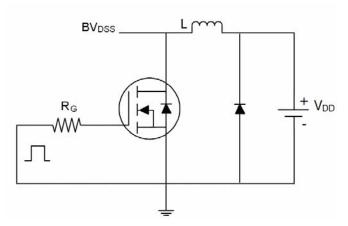
- ${\it 1. Repetitive Rating: Pulse width limited by maximum junction temperature.}\\$
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

**Pb Free Product** 

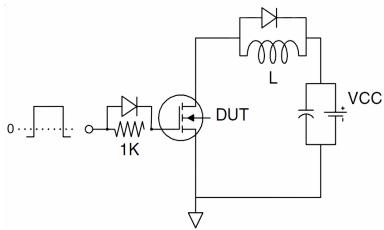


### **Test Circuit**

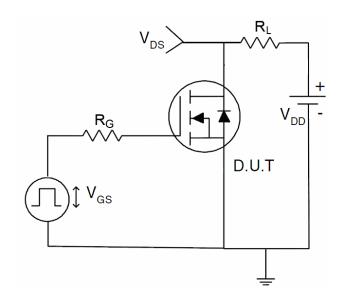
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit



## 3) Switch Time Test Circuit

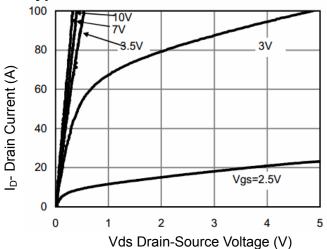


**Pb Free Product** 

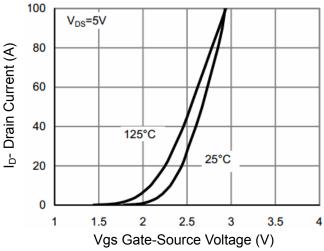


# NCEP0160A

### Typical Electrical and Thermal Characteristics



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

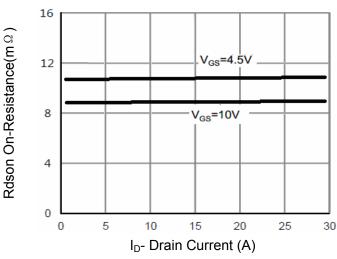
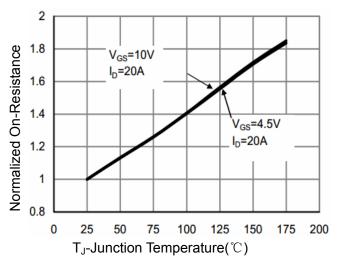


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

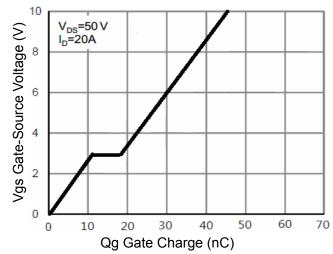


Figure 5 Gate Charge

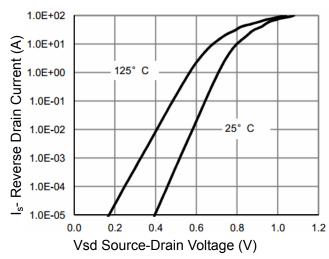
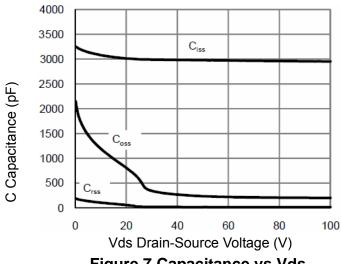
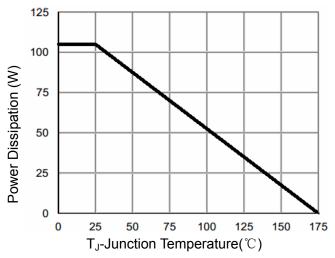
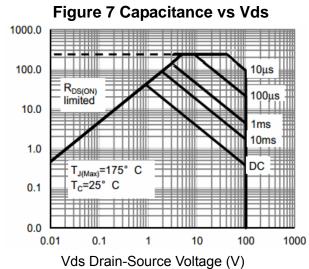


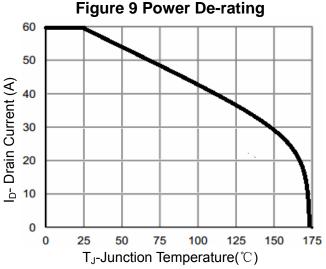
Figure 6 Source- Drain Diode Forward

Ip- Drain Current (A)



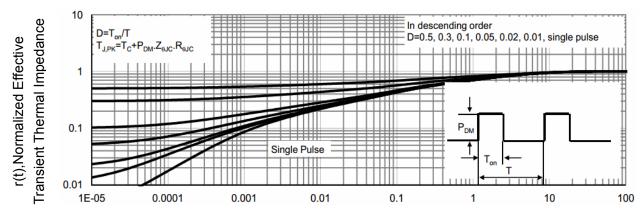






**Figure 8 Safe Operation Area** 





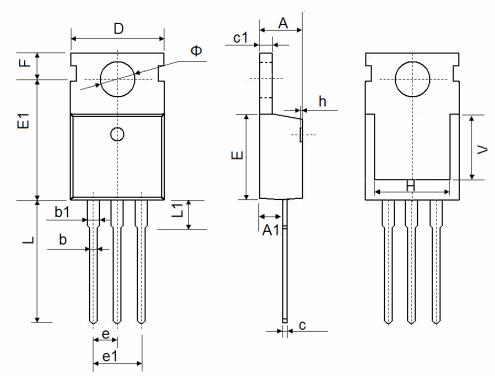
Square Wave Pluse Duration(sec)

**Figure 11 Normalized Maximum Transient Thermal Impedance** 

**Pb Free Product** 



## **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	2.540 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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